



Docket No. 740756-1974

UNITED STATES PATENT AND TRADEMARK OFFICE

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In re PATENT Application of: )  
Yasuhiko TAKEMURA et al. ) Art Unit 2822  
Application Serial No. 09/321,715 / ) Examiner: M. Wilczewski  
Filed: May 28, 1999 )  
For: SEMICONDUCTOR DEVICE AND PROCESS )  
FOR FABRICATING THE SAME )

AMENDMENT UNDER 37 C.F.R. 1.116

CERTIFICATE OF MAILING

Box AF  
Commissioner for Patents  
Washington, D.C. 20231

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on March 20, 2002

Sir:

Gwyn J. Cantrell

Responsive to the final Office Action mailed November 27, 2001, the period for responding having been extended one (1) month, please amend the above identified application as follows.

IN THE CLAIMS:

Please cancel claims 2, 10, 18, 26, 34 and 42.

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Please amend the claims as follows.

1. (Four Times Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:  
forming a semiconductor film comprising silicon over a glass substrate;  
crystallizing said semiconductor film; and  
oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atmosphere at a pressure greater than one atmosphere up to 15 atmospheres and at a temperature lower than a strain point of said glass substrate.